

XBS303V17R-G

Schottky Barrier Diode, 3A, 30V Type

FEATURES

- Forward Voltage : $V_F=0.355V$ (TYP.)
- Forward Current : $I_{F(AVE)}=3A$
- Repetitive Peak Reverse Voltage : $V_{RM}=30V$

APPLICATIONS

- Rectification
- Protection against reverse connection of battery

ABSOLUTE MAXIMUM RATINGS

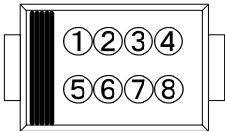
$T_a=25^\circ C$

PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage	V_{RM}	30	V
Reverse Voltage (DC)	V_R	30	V
Forward Current (Average)	$I_{F(AVE)}$	3	A
Non Continuous Forward Surge Current ^{*1}	I_{FSM}	60	A
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~+150	$^\circ C$

*1 : Non continuous high amplitude 60Hz half-sine wave.

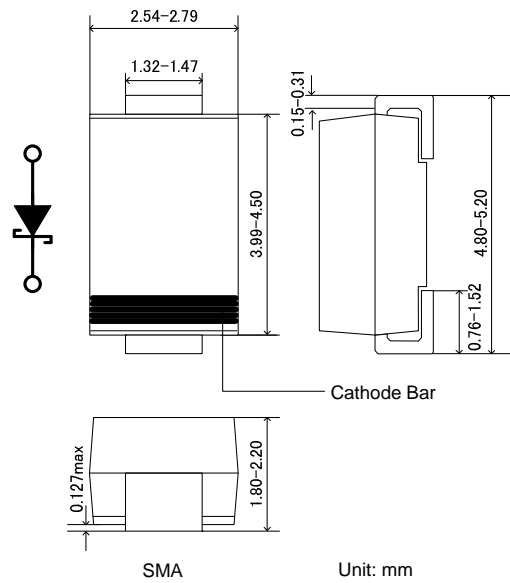
* When the IC is operated continuously under high load conditions such as high temperature, high current and high voltage, it may have the case that reliability reduces drastically even if under the absolute maximum ratings. Adequate "Derating" should be taken into consideration while designing.

MARKING RULE



①②③④⑤⑥: 303V17(Product Number)
⑦⑧ : Assembly Lot Number

PACKAGING INFORMATION



PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION
XBS303V17R-G	SMA (Halogen & Antimony free)
XBS303V17R	SMA

* The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

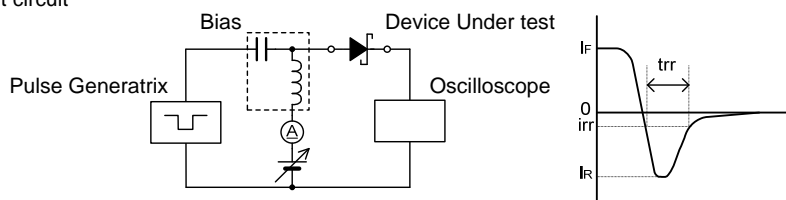
* The device orientation is fixed in its embossed tape pocket.

ELECTRICAL CHARACTERISTICS

$T_a=25^\circ C$

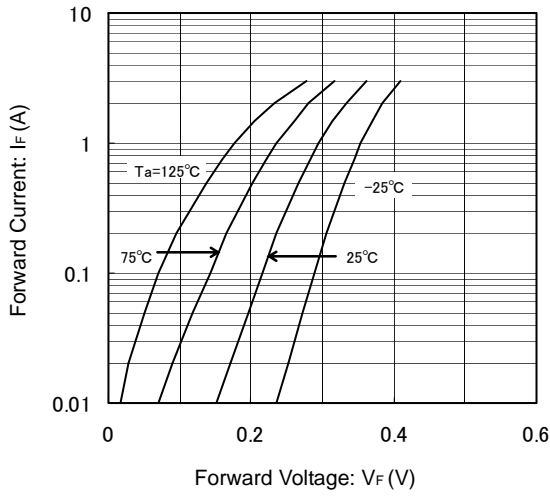
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	
Forward Voltage	V_{F1}	$I_F=0.5A$	-	0.265	0.34	V
	V_{F2}	$I_F=1A$	-	0.295	0.36	V
	V_{F3}	$I_F=3A$	-	0.355	0.39	V
Reverse Current	I_R	$V_R=30V$	-	0.35	3	mA
Inter-Terminal Capacity	C_t	$V_R=1V, f=1MHz$	-	385	-	pF
Reverse Recovery Time ^{*2}	t_{rr}	$I_F=I_R=10mA, i_{rr}=1mA$	-	90	-	ns

*2 : t_{rr} measurement circuit

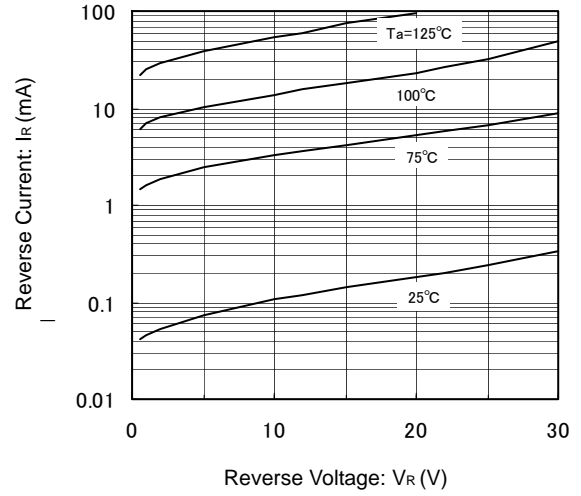


TYPICAL PERFORMANCE CHARACTERISTICS

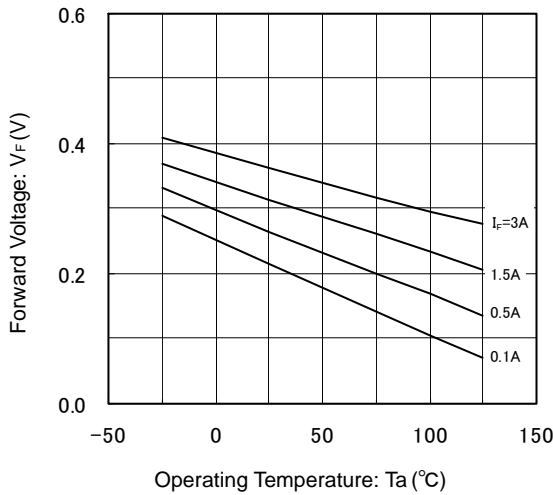
(1) Forward Current vs. Forward Voltage



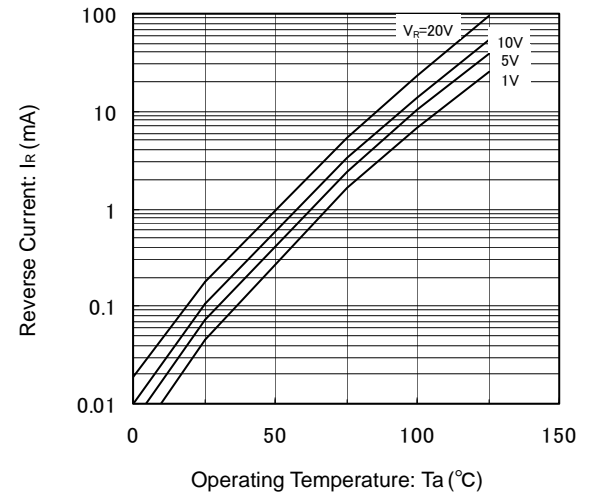
(2) Reverse Current vs. Reverse Voltage



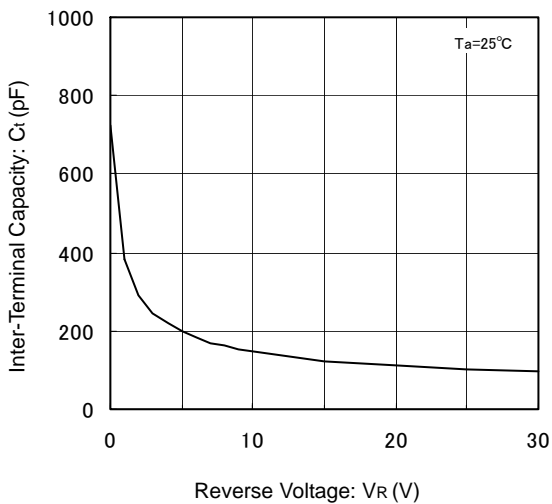
(3) Forward Voltage vs. Operating Temperature



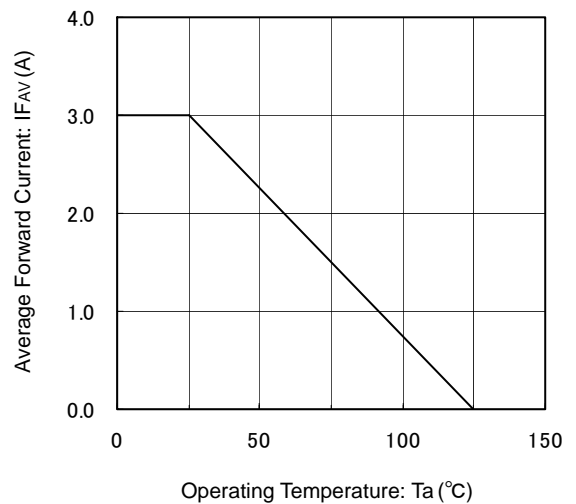
(4) Reverse Current vs. Operating Temperature



(5) Inter-Terminal Capacity vs. Reverse Voltage



(6) Average Forward Current vs. Operating Temperature



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